



# SHENZHEN HAOHUI MICRO-ELECTRONICS CO.,LTD

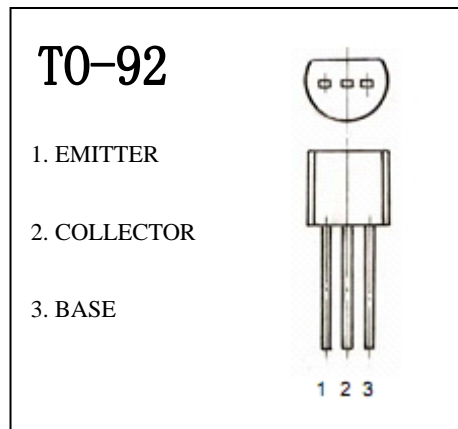
## TO-92 Plastic-Encapsulate Transistors

8550SS

TRANSISTOR(PNP)

MAXIMUM RATINGS(Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
VCBO	Collector-Base Voltage	-40	V
VCEO	Collector-Emitter Voltage	-25	V
VEBO	Emitter-Base Voltage	-5	V
IC	Collector Current	-1.5	A
PC	Collector Power Dissipation	1000	mW
Tj	Junction Temperature	150	°C
Tstg	Storage Temperature	-55~150	°C



ELECTRICAL CHARACTERISTICS(Tamb=25°C unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR)CBO	IC=-100uA, IE=0	-40			V
Collector-emitter breakdown voltage	V(BR)CEO	IC=-1mA, IB=0	-25			V
Emitter-base breakdown voltage	V(BR)EBO	IC=-100uA, IC=0	-5			V
Collector cut-off current	ICBO	VCB=-40V, IE=0			-0.1	μA
Emitter cut-off current	IEBO	VEB=-5V, IC=0			-0.1	μA
DC current gain	HFE(1)	Vce=-1V, IC=-100mA	85		400	
	HFE(2)	Vce=-6V, IC=-800mA	40			
Collector-emitter saturation voltage	VCE(sat)	IC=-800mA, IB=-80mA			-0.5	V
Base-emitter saturation voltage	VBE(sat)	IC=-800mA, IB=-80mA			-1.2	V
Base-emitter voltage	VBE	VCE=-1V, IC=-10mA			-1.0	V
Transition frequency	fT	VCE=-10V, IC=50Ma, f=30MH Z	100			MHz